

# ON Semiconductor

## Is Now



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# BUL44G

## SWITCHMODE™ NPN Bipolar Power Transistor

### For Switching Power Supply Applications

The BUL44G have an applications specific state-of-the-art die designed for use in 220 V line operated Switchmode Power supplies and electronic light ballasts.

#### Features

- Improved Efficiency Due to Low Base Drive Requirements:
  - High and Flat DC Current Gain  $h_{FE}$
  - Fast Switching
  - No Coil Required in Base Circuit for Turn-Off (No Current Tail)
- Full Characterization at 125°C
- Tight Parametric Distributions are Consistent Lot-to-Lot
- These Devices are Pb-Free and are RoHS Compliant\*

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Sustaining Voltage	$V_{CEO}$	400	Vdc
Collector-Base Breakdown Voltage	$V_{CES}$	700	Vdc
Emitter-Base Voltage	$V_{EBO}$	9.0	Vdc
Collector Current <ul style="list-style-type: none"><li>– Continuous</li><li>– Peak (Note 1)</li></ul>	$I_C$ $I_{CM}$	2.0 5.0	Adc
Base Current <ul style="list-style-type: none"><li>– Continuous</li><li>– Peak (Note 1)</li></ul>	$I_B$ $I_{BM}$	1.0 2.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	$P_D$	50 0.4	W W/°C
Operating and Storage Temperature	$T_J, T_{stg}$	–65 to 150	°C

#### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 5 Seconds	$T_L$	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

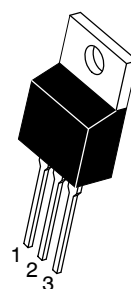
1. Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.



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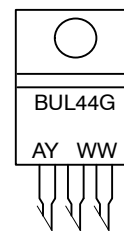
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### POWER TRANSISTOR 2.0 AMPERES, 700 VOLTS, 40 AND 100 WATTS



TO-220AB  
CASE 221A-09  
STYLE 1

#### MARKING DIAGRAM



BUL44 = Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

#### ORDERING INFORMATION

Device	Package	Shipping
BUL44G	TO-220 (Pb-Free)	50 Units / Rail

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# BUL44G

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage (I <sub>C</sub> = 100 mA, L = 25 mH)	V <sub>CEO(sus)</sub>	400	–	–	Vdc
Collector Cutoff Current (V <sub>CE</sub> = Rated V <sub>CEO</sub> , I <sub>B</sub> = 0)	I <sub>CEO</sub>	–	–	100	μAdc
Collector Cutoff Current (V <sub>CE</sub> = Rated V <sub>CES</sub> , V <sub>EB</sub> = 0) (V <sub>CE</sub> = 500 V, V <sub>EB</sub> = 0)	I <sub>CES</sub>	– – –	– – –	100 500 100	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 9.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	–	100	μAdc

### ON CHARACTERISTICS

Base-Emitter Saturation Voltage (I <sub>C</sub> = 0.4 Adc, I <sub>B</sub> = 40 mAdc) (I <sub>C</sub> = 1.0 Adc, I <sub>B</sub> = 0.2 Adc)	V <sub>BE(sat)</sub>	– –	0.85 0.92	1.1 1.25	Vdc
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 0.4 Adc, I <sub>B</sub> = 40 mAdc)  (I <sub>C</sub> = 1.0 Adc, I <sub>B</sub> = 0.2 Adc)	V <sub>CE(sat)</sub>	– – –	0.20 0.20 0.25 0.25	0.5 0.5 0.6 0.6	Vdc
DC Current Gain (I <sub>C</sub> = 0.2 Adc, V <sub>CE</sub> = 5.0 Vdc)  (I <sub>C</sub> = 0.4 Adc, V <sub>CE</sub> = 1.0 Vdc)  (I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 1.0 Vdc)  (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 5.0 Vdc)	h <sub>FE</sub>	14 – 12 12 8.0 7.0 10	– 32 20 20 14 13 22	34 – – – – – –	–

### DYNAMIC CHARACTERISTICS

Current Gain Bandwidth (I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 1.0 MHz)				f <sub>T</sub>	–	13	–	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)				C <sub>OB</sub>	–	38	60	pF
Input Capacitance (V <sub>EB</sub> = 8.0 V)				C <sub>IB</sub>	–	380	600	pF
Dynamic Saturation Voltage: Determined 1.0 μs and 3.0 μs respectively after rising I <sub>B1</sub> reaches 90% of final I <sub>B1</sub>	(I <sub>C</sub> = 0.4 Adc I <sub>B1</sub> = 40 mAdc V <sub>CC</sub> = 300 V)	1.0 μs	(T <sub>C</sub> = 125°C)	V <sub>CE(dsat)</sub>	– –	2.5 2.7	– –	Vdc
		3.0 μs	(T <sub>C</sub> = 125°C)		– –	1.3 1.15	– –	
	(I <sub>C</sub> = 1.0 Adc I <sub>B1</sub> = 0.2 Adc V <sub>CC</sub> = 300 V)	1.0 μs	(T <sub>C</sub> = 125°C)		– –	3.2 7.5	– –	
		3.0 μs	(T <sub>C</sub> = 125°C)		– –	1.25 1.6	– –	

# BUL44G

## SWITCHING CHARACTERISTICS: Resistive Load (D.C. $\leq 10\%$ , Pulse Width = 20 $\mu\text{s}$ )

Turn-On Time	$(I_C = 0.4 \text{ Adc}, I_{B1} = 40 \text{ mAdc}$ $I_{B2} = 0.2 \text{ Adc}, V_{CC} = 300 \text{ V})$ ( $T_C = 125^\circ\text{C}$ )	$t_{on}$	–	40	100	ns
Turn-Off Time		$t_{off}$	–	40	–	–
Turn-On Time	$(I_C = 0.4 \text{ Adc}, I_{B1} = 40 \text{ mAdc}$ $I_{B2} = 0.2 \text{ Adc}, V_{CC} = 300 \text{ V})$ ( $T_C = 125^\circ\text{C}$ )	$t_{on}$	–	1.5	2.5	$\mu\text{s}$
Turn-Off Time		$t_{off}$	–	2.0	–	–
Turn-On Time	$(I_C = 1.0 \text{ Adc}, I_{B1} = 0.2 \text{ Adc}$ $I_{B1} = 0.5 \text{ Adc}, V_{CC} = 300 \text{ V})$ ( $T_C = 125^\circ\text{C}$ )	$t_{on}$	–	85	150	ns
Turn-Off Time		$t_{off}$	–	85	–	–
Turn-On Time	$(I_C = 1.0 \text{ Adc}, I_{B1} = 0.2 \text{ Adc}$ $I_{B2} = 0.5 \text{ Adc}, V_{CC} = 300 \text{ V})$ ( $T_C = 125^\circ\text{C}$ )	$t_{on}$	–	1.75	2.5	$\mu\text{s}$
Turn-Off Time		$t_{off}$	–	2.10	–	–

## SWITCHING CHARACTERISTICS: Inductive Load ( $V_{clamp} = 300 \text{ V}$ , $V_{CC} = 15 \text{ V}$ , $L = 200 \mu\text{H}$ )

Fall Time	$(I_C = 0.4 \text{ Adc}, I_{B1} = 40 \text{ mAdc}$ $I_{B2} = 0.2 \text{ Adc})$ ( $T_C = 125^\circ\text{C}$ )	$t_{fi}$	–	125	200	ns
Storage Time		$t_{si}$	–	120	–	–
Crossover Time		$t_c$	–	0.7	1.25	$\mu\text{s}$
Fall Time	$(I_C = 0.4 \text{ Adc}, I_{B1} = 40 \text{ mAdc}$ $I_{B2} = 0.2 \text{ Adc})$ ( $T_C = 125^\circ\text{C}$ )	$t_{fi}$	–	0.8	–	–
Storage Time		$t_{si}$	–	110	200	ns
Crossover Time		$t_c$	–	110	–	–
Fall Time	$(I_C = 1.0 \text{ Adc}, I_{B1} = 0.2 \text{ Adc}$ $I_{B2} = 0.5 \text{ Adc})$ ( $T_C = 125^\circ\text{C}$ )	$t_{fi}$	–	110	175	ns
Storage Time		$t_{si}$	–	120	–	–
Crossover Time		$t_c$	–	1.7	2.75	$\mu\text{s}$
Fall Time	$(I_C = 1.0 \text{ Adc}, I_{B1} = 0.2 \text{ Adc}$ $I_{B2} = 0.5 \text{ Adc})$ ( $T_C = 125^\circ\text{C}$ )	$t_{fi}$	–	2.25	–	–
Storage Time		$t_{si}$	–	180	300	ns
Crossover Time		$t_c$	–	210	–	–
Fall Time	$(I_C = 0.8 \text{ Adc}, I_{B1} = 160 \text{ mAdc}$ $I_{B2} = 160 \text{ mAdc})$ ( $T_C = 125^\circ\text{C}$ )	$t_{fi}$	70	–	170	ns
Storage Time		$t_{si}$	–	180	–	–
Crossover Time		$t_c$	–	2.6	3.8	$\mu\text{s}$
Fall Time	$(I_C = 0.8 \text{ Adc}, I_{B1} = 160 \text{ mAdc}$ $I_{B2} = 160 \text{ mAdc})$ ( $T_C = 125^\circ\text{C}$ )	$t_{fi}$	2.6	–	–	–
Storage Time		$t_{si}$	–	4.2	–	–
Crossover Time		$t_c$	–	190	300	ns
Fall Time	$(I_C = 0.8 \text{ Adc}, I_{B1} = 160 \text{ mAdc}$ $I_{B2} = 160 \text{ mAdc})$ ( $T_C = 125^\circ\text{C}$ )	$t_{fi}$	–	350	–	–
Storage Time		$t_{si}$	–	–	–	–
Crossover Time		$t_c$	–	–	–	–

TYPICAL STATIC CHARACTERISTICS

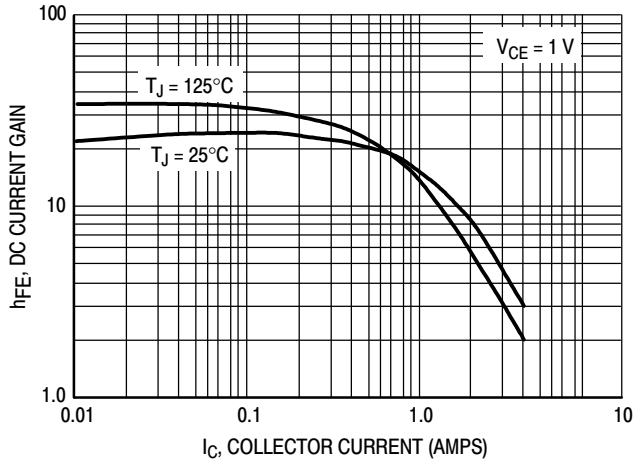


Figure 1. DC Current Gain at 1 Volt

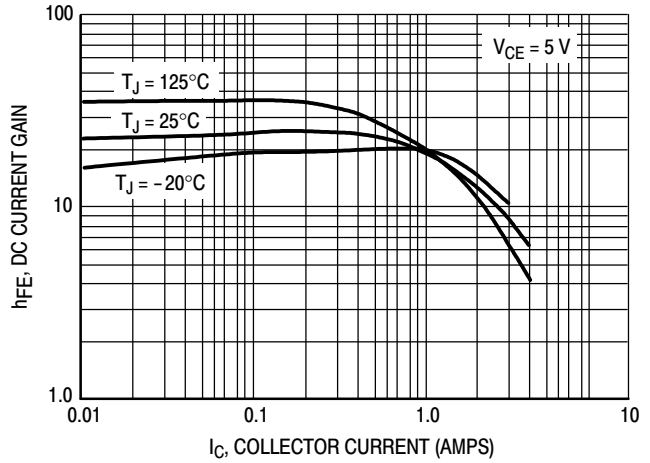


Figure 2. DC Current Gain at 5 Volts

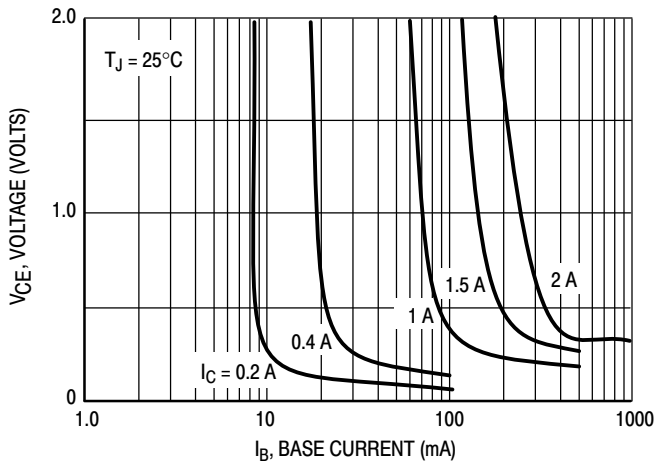


Figure 3. Collector Saturation Region

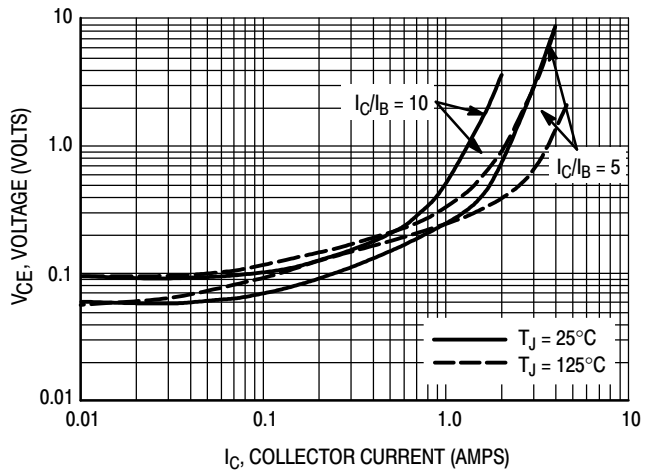


Figure 4. Collector-Emitter Saturation Voltage

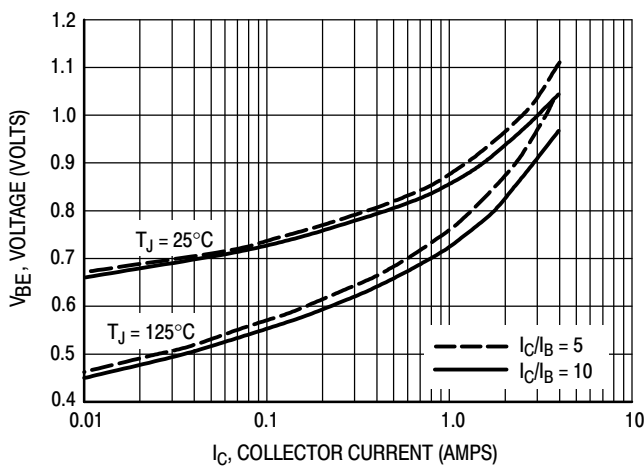


Figure 5. Base-Emitter Saturation Region

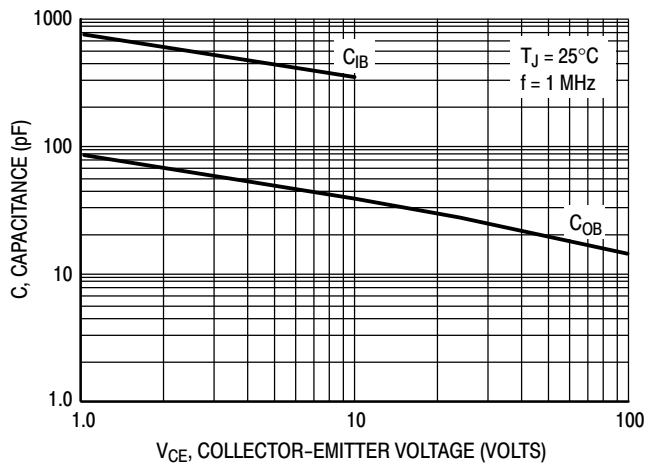


Figure 6. Capacitance

**TYPICAL SWITCHING CHARACTERISTICS**  
( $I_{B2} = I_C/2$  for all switching)

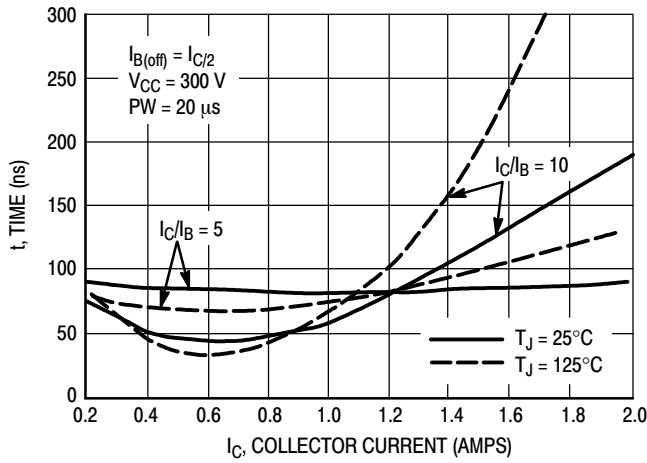


Figure 7. Resistive Switching,  $t_{on}$

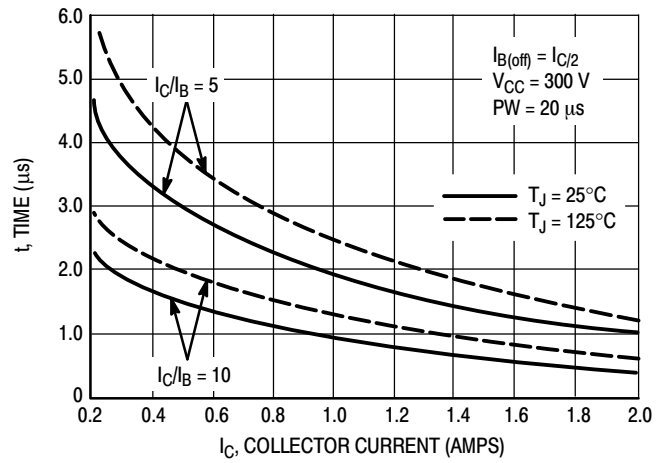


Figure 8. Resistive Switching,  $t_{off}$

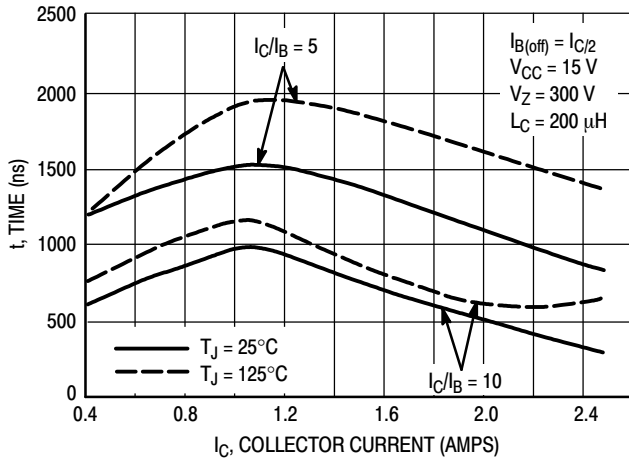


Figure 9. Inductive Storage Time,  $t_{si}$

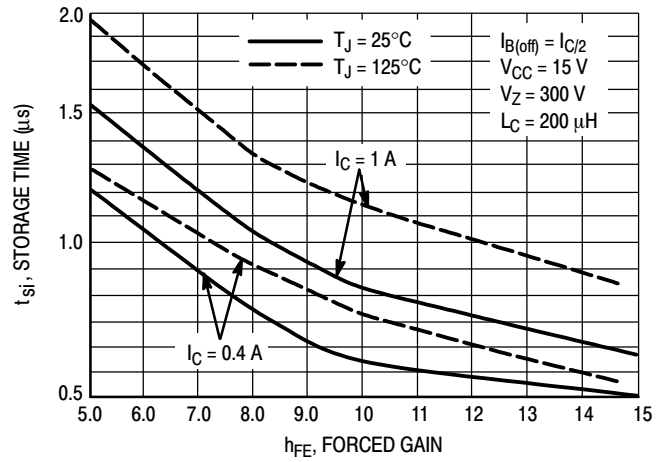


Figure 10. Inductive Storage Time

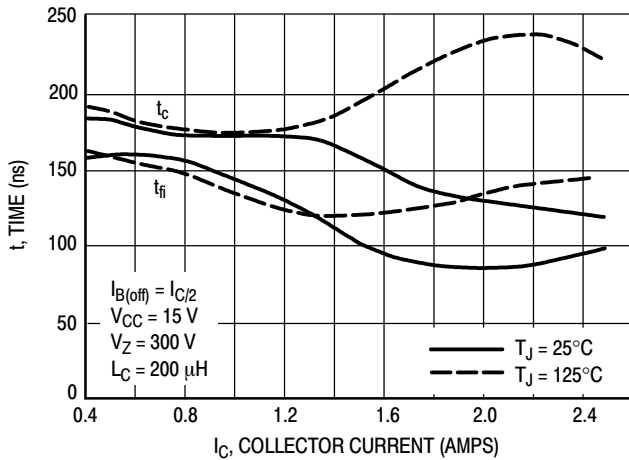


Figure 11. Inductive Switching,  $t_c$  and  $t_{fi}$   $I_C/I_B = 5$

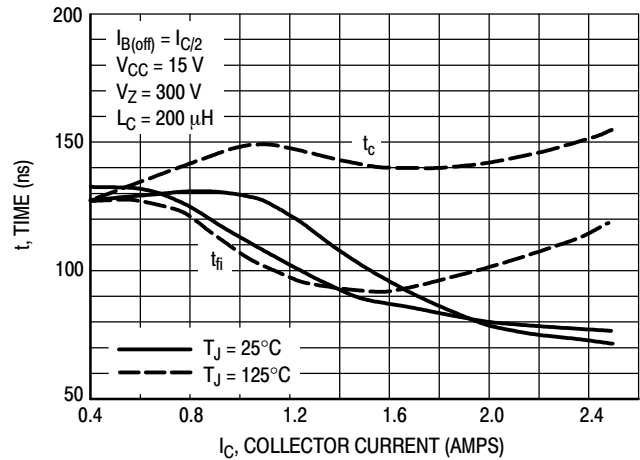
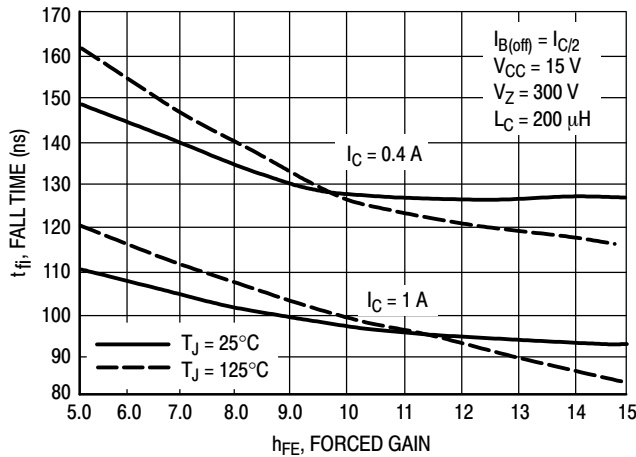
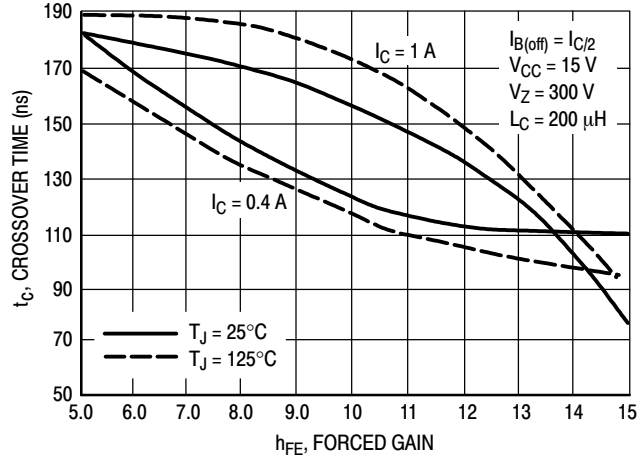


Figure 12. Inductive Switching,  $t_c$  and  $t_{fi}$   $I_C/I_B = 10$

**TYPICAL SWITCHING CHARACTERISTICS**  
( $I_{B2} = I_C/2$  for all switching)

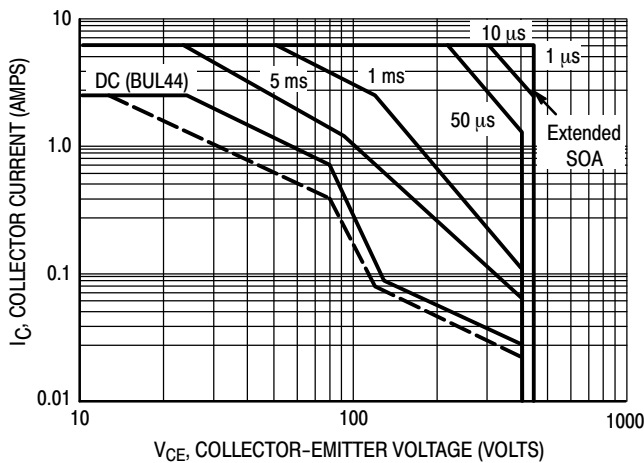


**Figure 13. Inductive Fall Time**

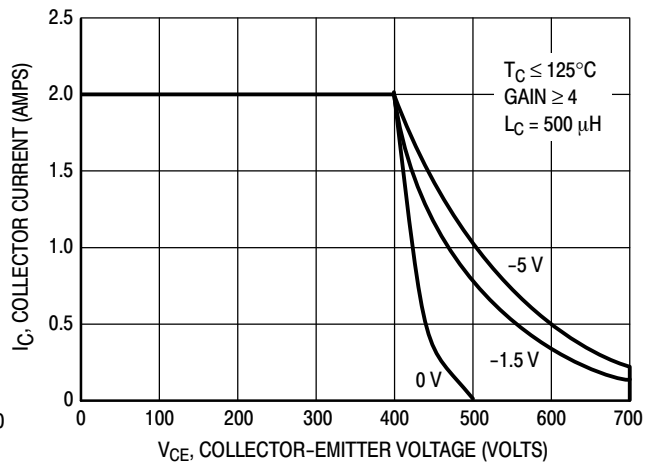


**Figure 14. Inductive Crossover Time**

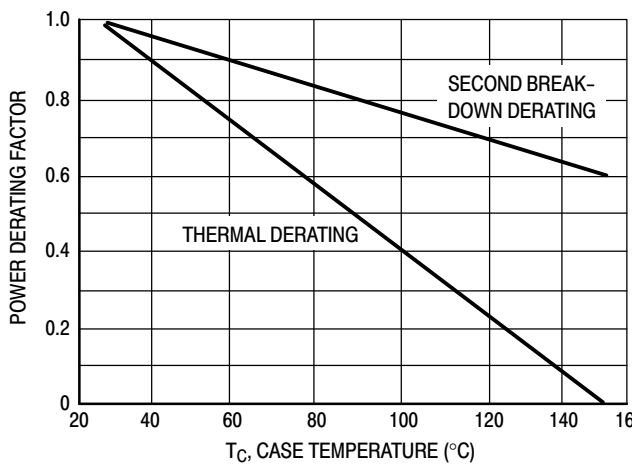
**GUARANTEED SAFE OPERATING AREA INFORMATION**



**Figure 15. Forward Bias Safe Operating Area**



**Figure 16. Reverse Bias Switching Safe Operating Area**



**Figure 17. Forward Bias Power Derating**

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C$ - $V_{CE}$

limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of figure 15 is based on  $T_C = 25^\circ\text{C}$ ;  $T_{J(PK)}$  is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when  $T_C > 25^\circ\text{C}$ . Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on figure 15 may be found at any case temperature by using the appropriate curve on figure 17.  $T_{J(PK)}$  may be calculated from the data in figure 20. At any case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown. For inductive loads, high voltage and current must be sustained simultaneously during turn-off with the base-to-emitter junction reverse-biased. The safe level is specified as a reverse-biased safe operating area (Figure 16). This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode.

# BUL44G

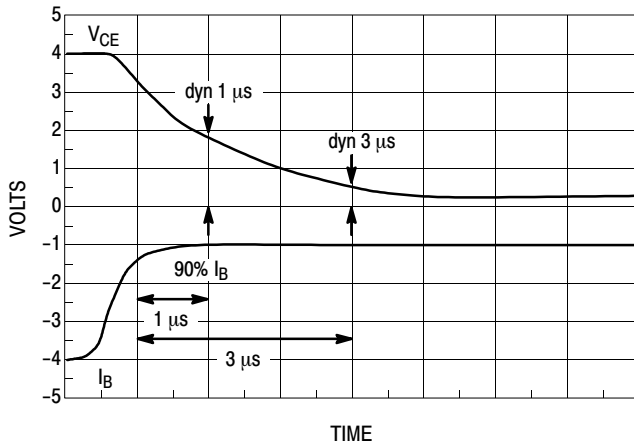


Figure 18. Dynamic Saturation Voltage Measurements

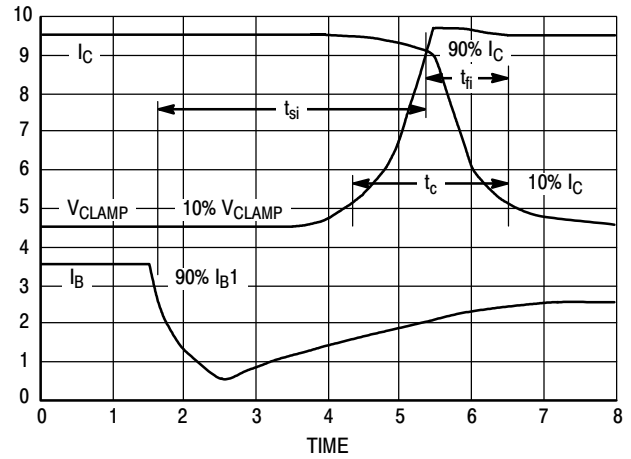


Figure 19. Inductive Switching Measurements

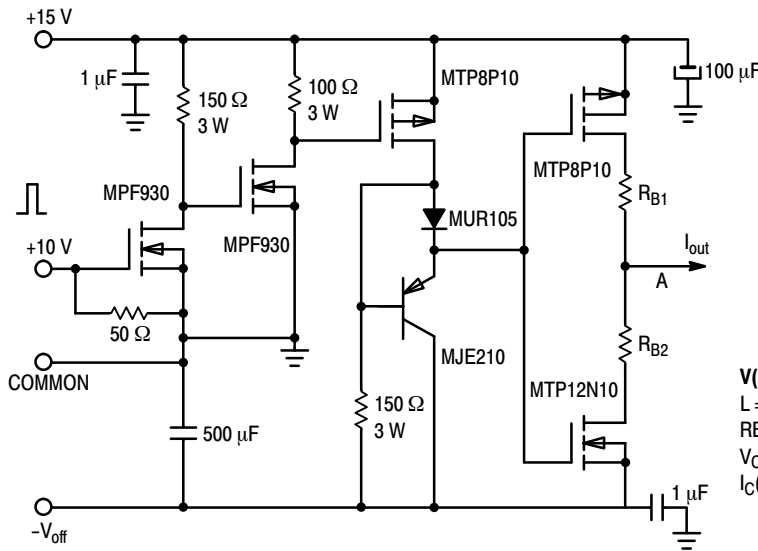


Table 1. Inductive Load Switching Drive Circuit

V(BR)CEO(sus)	INDUCTIVE SWITCHING	RBSOA
L = 10 mH	L = 200 μH	L = 500 μH
RB2 = ∞	RB2 = 0	RB2 = 0
V <sub>CC</sub> = 20 VOLTS	V <sub>CC</sub> = 15 VOLTS	V <sub>CC</sub> = 15 VOLTS
I <sub>C(pk)</sub> = 100 mA	RB1 SELECTED FOR DESIRED I <sub>B1</sub>	RB1 SELECTED FOR DESIRED I <sub>B1</sub>

## TYPICAL THERMAL RESPONSE

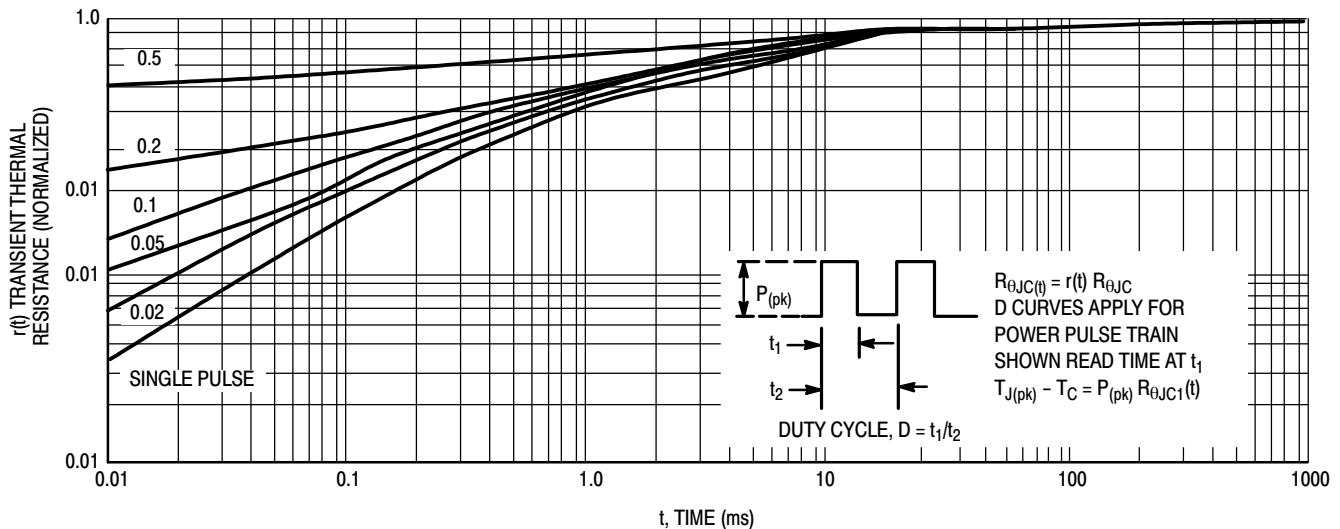


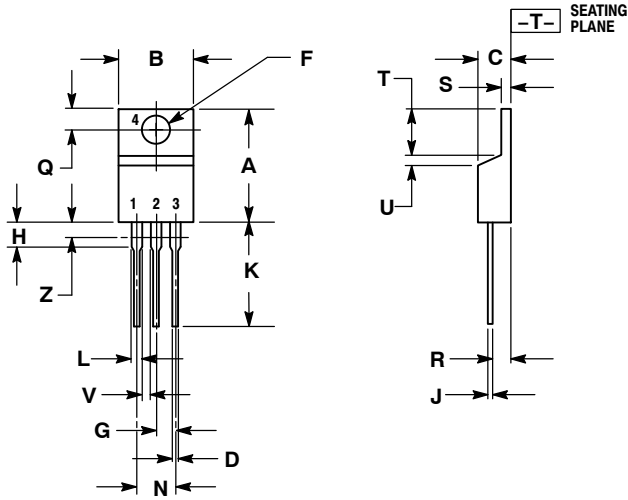
Figure 20. Typical Thermal Response ( $Z_{\theta JC}(t)$ ) for BUL44



# BUL44G

## PACKAGE DIMENSIONS

TO-220AB  
CASE 221A-09  
ISSUE AF



### NOTES:


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

### STYLE 1:

1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

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